Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 07977-004002	Application No. 10/602,762
Corrected Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Naoto Kusumoto et al.	
		Filing Date June 25, 2003	Group Art Unit 2828

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
DMR	AA	3,585,088	06/1971	Scwuttke et al.			
	AB	4,195,913	4/1/80	Dourte et al.			
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	AW	1-76715	03/1989	Japan				
DMR	AX	3-286518	12/1991	Japan				

Examiner Signature	Date Considered
	4/05

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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[signature]	4/05

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